

3. (Twice Amended) The method as claimed in claim 8,  
wherein  
the auxiliary layer is used at least partly as a hard mask for the patterning and  
preceding the etching by dry etching.
4. (Twice Amended) The method as claimed in claim 8,  
wherein  
the auxiliary layer is detected by an etching stop detection signal during the CMP  
process.
5. (Twice Amended) The method as claimed in claim 8,  
wherein  
an additional wet-chemical cleaning step is carried out at the end of the etching.
6. (Twice Amended) The method as claimed in claim 8,  
wherein  
the auxiliary layer is composed of diamond-like carbon, carbon polymers or of  
porous material.

Please add new claim 8 as follows:

- B2
8. (New) A method for producing a metal contact in a dielectric comprising the steps of:
- forming a contact via in said dielectric;
- providing a liner made of titanium or a titanium compound on the whole area of said dielectric and in said contact via;
- providing a metalization on said whole area, on said dielectric and in said contact via, wherein at least in the surroundings of said contact via, an auxiliary layer is provided on said dielectric between said dielectric and said liner, said auxiliary layer being removable by a Chemical Mechanical Polishing process; and
- removing said metalization on said liner and said auxiliary layer by said Chemical Mechanical Polishing process, said process stopping on said dielectric, whereby upon a breakthrough of said liner an under etch of said liner by removal of said auxiliary layer is effected such that the liner lying thereon is lifted off.